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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE MAIL ROOM

In re application of

Kiyoshi TAKEI, et al.

Appln. No.: 09/482,099

Group Art Unit: 2877

Confirmation No.: Unknown

Examiner: Delma R. Flores Ruiz

Filed: January 13, 2000

For: DISTRIBUTED FEEDBACK TYPE SEMICONDUCTOR LASER DEVICE (As Amended)

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated November 8, 2001, please amend the above-identified application as follows:

IN THE TITLE:

Please delete the present title and replace it with the following new title:

DISTRIBUTED FEEDBACK TYPE SEMICONDUCTOR LASER DEVICE

IN THE SPECIFICATION:

Please enter the following changes:

Please delete the paragraph bridging pages 7 and 8 and insert therefor:

Subsequently, as shown in Figs. 5 and 6, a silicon compound or the like is coated on the grating layer 7a and cured to form the inorganic protective layers 8. Further, a resist mask 13 composed of SiO₂, TiO₂ and so on is applied on the protective layers to leave gaps in a strip shape in the direction [011] of the InP crystal substrate 1. The gaps define a transverse width of the through grooves or gap 8a, which is associated in confining the light, generated in the

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